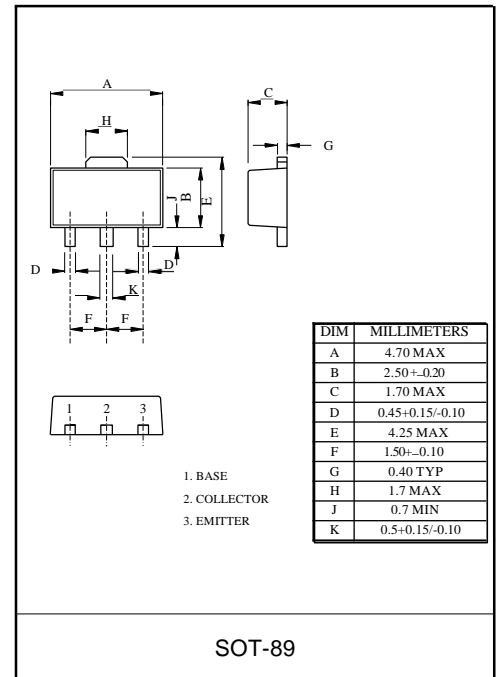


2SC2383TQ

FEATURES

Silicon NPN transistor in a SOT-89 Plastic Package

Color TV class B sound output applications



Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	160	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current-Continuous	I_C	1.0	A
Collector Base-Continuous	I_B	0.5	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	160			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=150V$ $I_E=0$			1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=6.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=200mA$	60		320	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA$ $I_B=50mA$			1.5	V
Emitter to Base Saturation Voltage	V_{BE}	$V_{CE}=5.0V$ $I_C=5.0mA$	0.45		0.75	V
Transition Frequency	f_T	$V_{CE}=5.0V$ $I_C=200mA$	20	100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $f=1.0MHz$ $I_E=0$			20	pF

h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	60~120	100~200	160~320
Marking	H83R	H83O	H83Y

: Ordering Method : 2SC2383TQ-R, 2SC2383TQ-O, 2SC2383TQ-Y

Electrical Characteristic Curve

